

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

NANDAKUMAR

Serial No. 09/252,514 (TI-23103)

Filed February 18, 1999

For: DUAL-COUNTERDOPED CHANNEL FIELD EFFECT TRANSISTOR AND METHOD

Art Unit 2811

Examiner J. Carroll

Commissioner for Patents
Washington, D. C. 20231

Sir:

AMENDMENT UNDER 37 C.F.R. 1.111

In response to the Office action dated August 8, 2000, please amend the above identified application as follows:

In the specification:

Page 3, line 14, after "that" add --a--.

In the claims:

Amend claim 1 as follows:

1. (Amended) A field effect transistor comprising:
- a region of semiconductor material doped a first conductivity type;
- a source of opposite conductivity type and a drain of opposite conductivity type, both
- disposed in said region of semiconductor material and separated by a channel region;



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